

EPIGAP Optronik GmbH

Koepenicker Str. 325
D-12555 Berlin
Fon: +49 (0)30 657637 60
Fax: +49 (0)30 657637 70
sales@epigap-optronic.de



Data Sheet

Preliminary

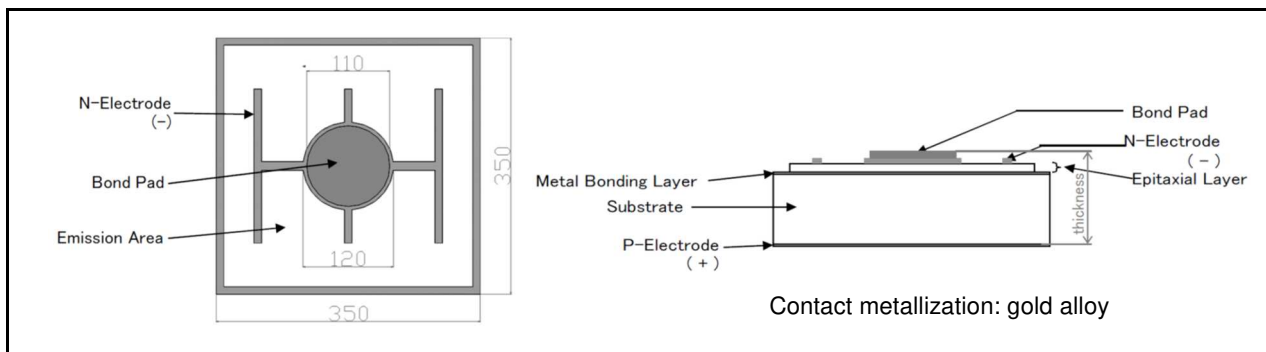
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Infrared LED Chip

EOLC-1200-27

Rev. 04, 2020

Radiation	Type	Electrodes
Infrared	InGaAs - based material, MQW	n (cathode) up



Die size (typ.): 0.350 mm × 0.350 mm (14 mil)

Thickness (typ.): 0.180 mm (7 mil)

Bond pad size: Ø 0.110 mm (periphery = Ø 0.120 mm)

Maximum Ratings

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Forward current		I _F	100	mA
Reverse voltage		V _R	5	V

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =20 mA	V _F		1.0		V
Radiant power*	I _F =20 mA	Φ _e		4.8		mW
Peak wavelength	I _F =20 mA	λ _p		1200		nm
FWHM	I _F =20 mA	Δλ _{0.5}		62		nm
Forward voltage	I _F =50 mA	V _F		1.1		V
Radiant power*	I _F =50 mA	Φ _e		9.6		mW
Forward voltage	I _F =100 mA	V _F		1.2		V
Radiant power*	I _F =100 mA	Φ _e		14.4		mW

*Measured on bare chip on TO-18 header

Packing

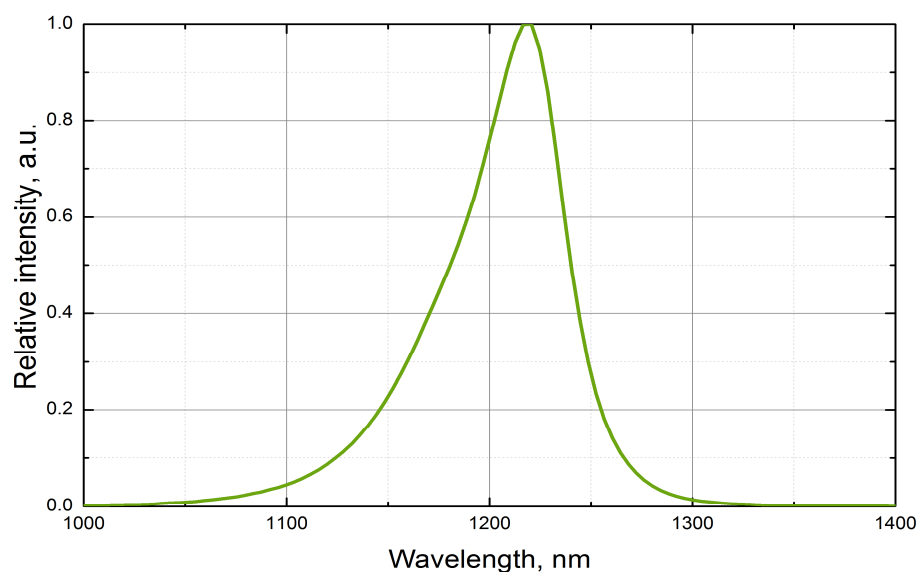
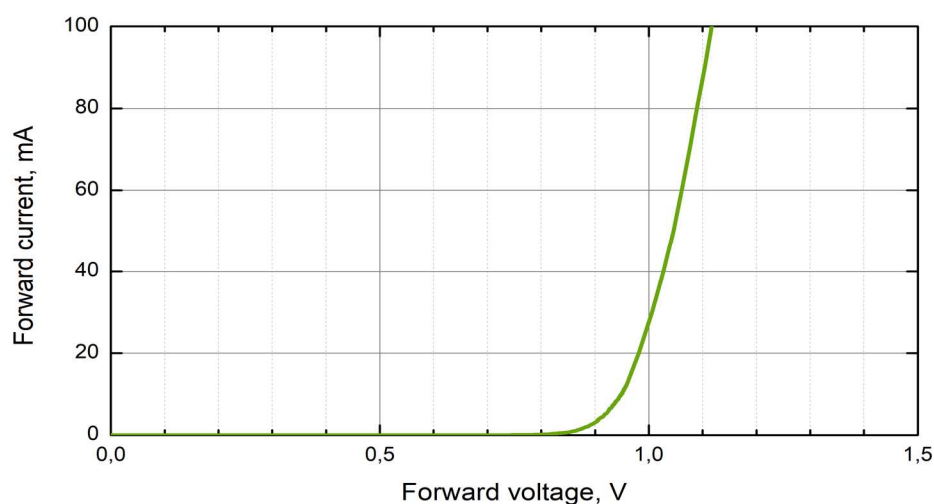
Dice on adhesive film with wire bond side up.



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.

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**Spectrum at 20 mA****Forward current vs. voltage**

Art. No. 113 165



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